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Kind regards,

Team Nexperia

PDTA114E series

PNP resistor-equipped transistors;
R1 = 10 k Ω , R2 = 10 k Ω

Rev. 10 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN complement	Package configuration
	NXP	JEITA	JEDEC		
PDTA114EE	SOT416	SC-75	-	PDTC114EE	ultra small
PDTA114EM	SOT883	SC-101	-	PDTC114EM	leadless ultra small
PDTA114ET	SOT23	-	TO-236AB	PDTC114ET	small
PDTA114EU	SOT323	SC-70	-	PDTC114EU	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs
- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

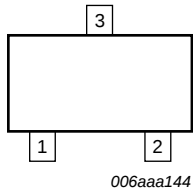
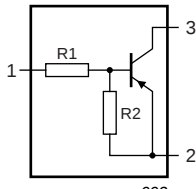
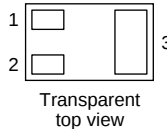
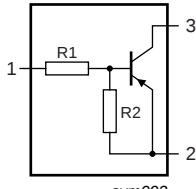
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	k Ω
R2/R1	bias resistor ratio		0.8	1.0	1.2	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT23; SOT323; SOT416			
1	input (base)	 006aaa144	 sym003
2	GND (emitter)		
3	output (collector)		
SOT883			
1	input (base)	 Transparent top view	 sym003
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTA114EE	SC-75	plastic surface-mounted package; 3 leads	SOT416
PDTA114EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.5 mm	SOT883
PDTA114ET	-	plastic surface-mounted package; 3 leads	SOT23
PDTA114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTA114EE	03
PDTA114EM	E5
PDTA114ET	*03
PDTA114EU	*03

[1] * = placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

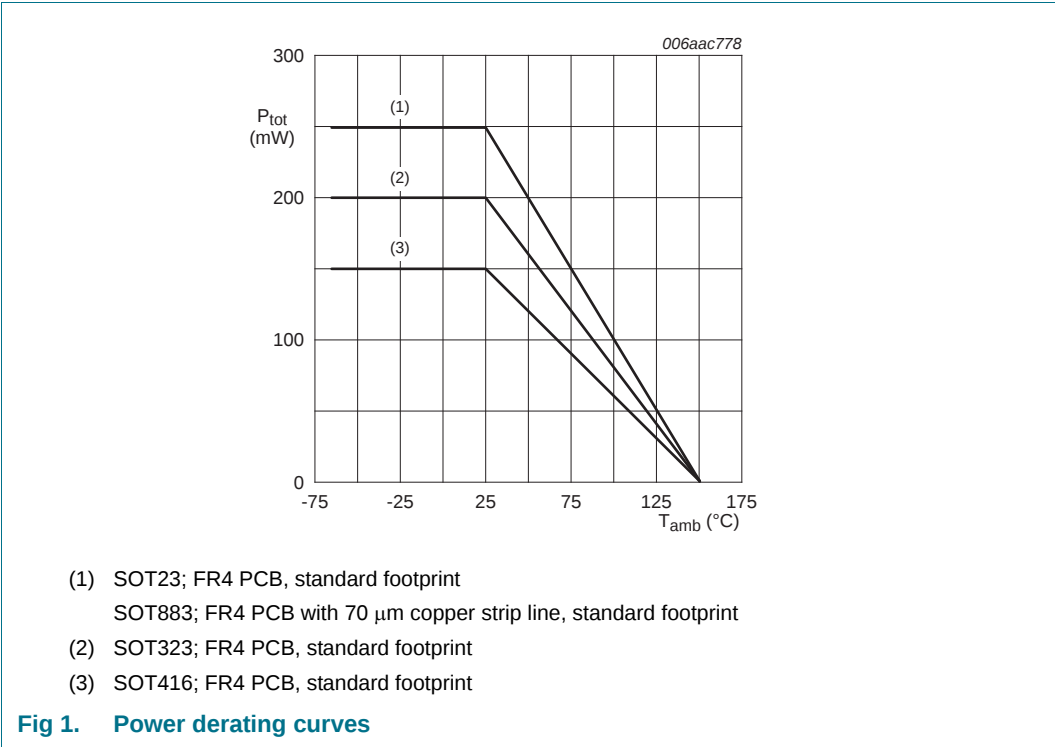
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
V _I	input voltage				
	positive		-	+40	V
	negative		-	-10	V
I _O	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	PDTA114EE (SOT416)		[1][2]	150	mW
	PDTA114EM (SOT883)		[2][3]	250	mW
	PDTA114ET (SOT23)		[1]	250	mW
	PDTA114EU (SOT323)		[1]	200	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 μ m copper strip line, standard footprint.

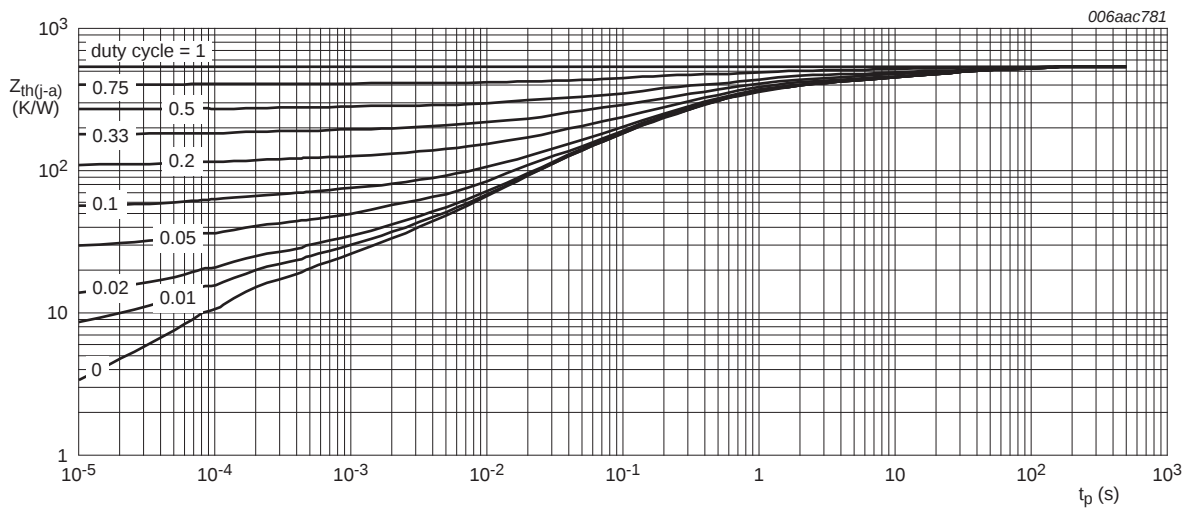


6. Thermal characteristics

Table 7. Thermal characteristics

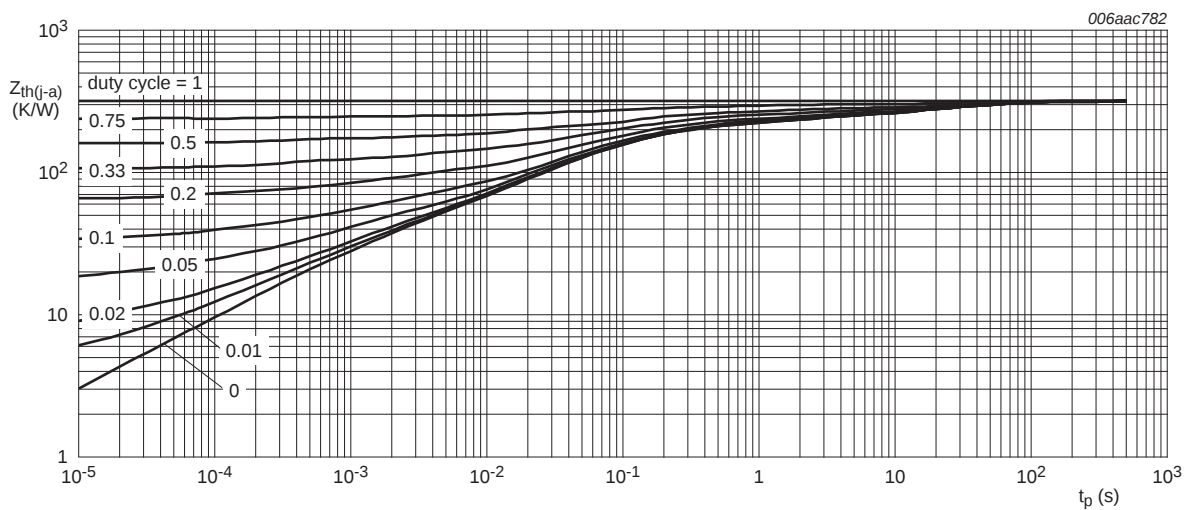
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA114EE (SOT416)	[1][2]	-	-	830	K/W
	PDTA114EM (SOT883)	[2][3]	-	-	500	K/W
	PDTA114ET (SOT23)	[1]	-	-	500	K/W
	PDTA114EU (SOT323)	[1]	-	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



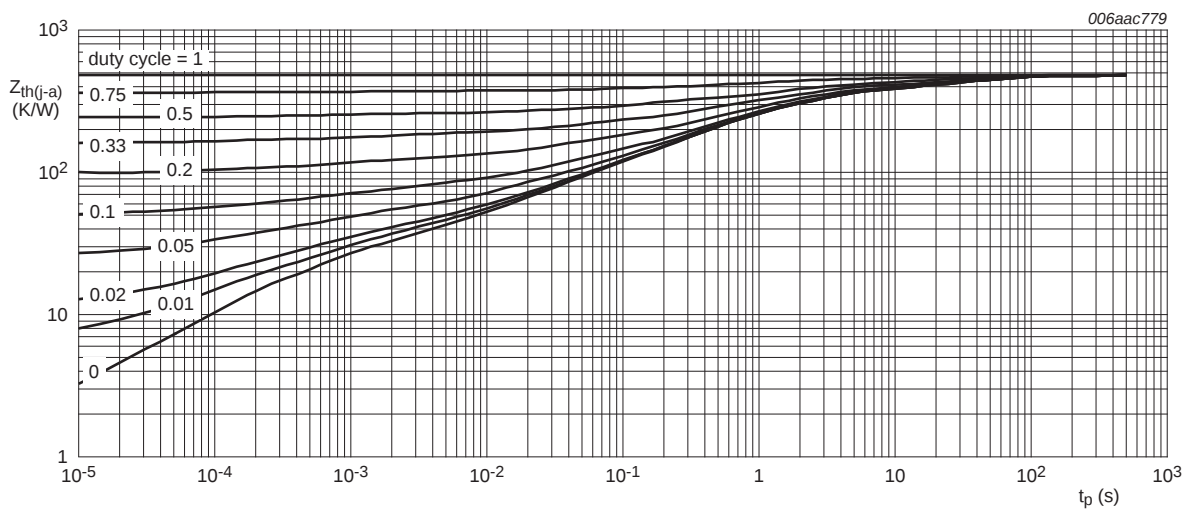
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EE (SOT416); typical values



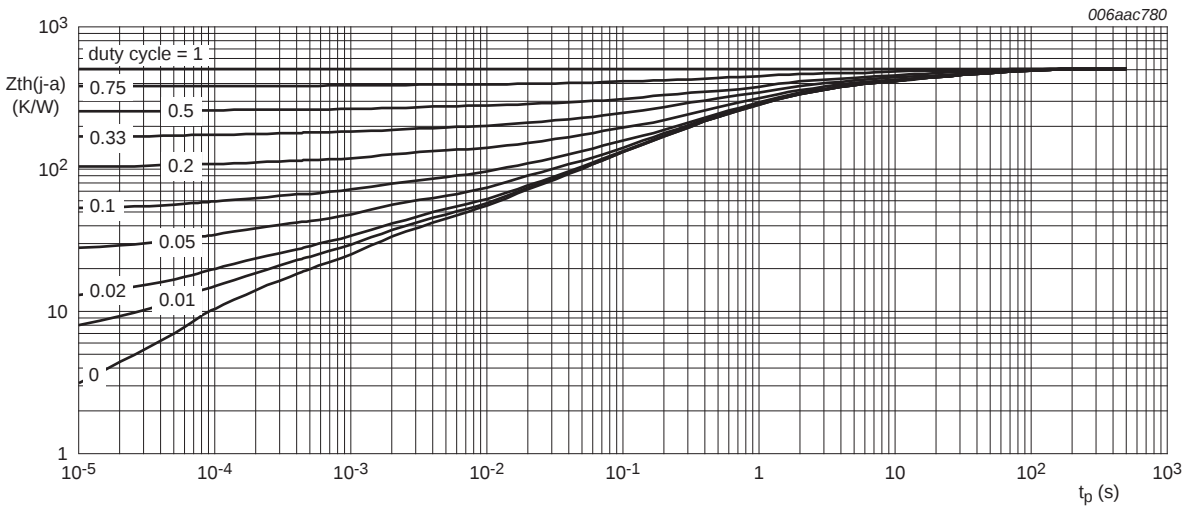
FR4 PCB, 70 μm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114ET (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EU (SOT323); typical values

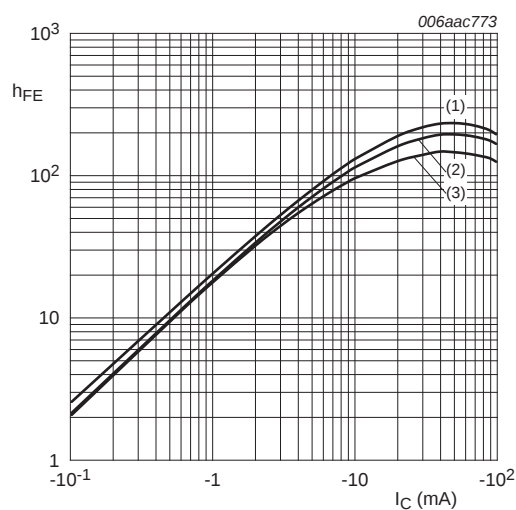
7. Characteristics

Table 8. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

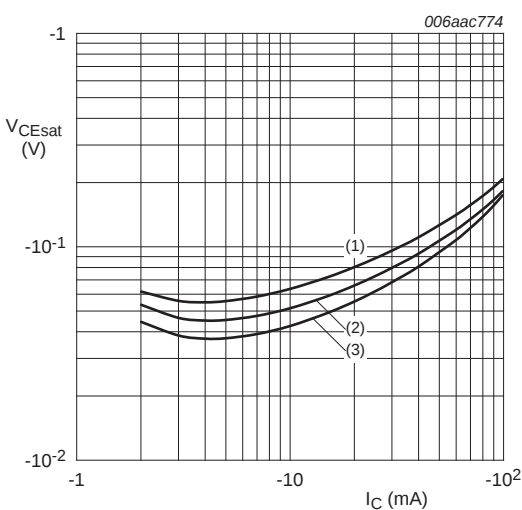
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -50\text{ V}$; $I_E = 0\text{ A}$	-	-	-100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}$; $I_B = 0\text{ A}$	-	-	-1	μA
		$V_{CE} = -30\text{ V}$; $I_B = 0\text{ A}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	-5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}$; $I_C = 0\text{ A}$	-	-	-400	μA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}$; $I_C = -5\text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -0.5\text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5\text{ V}$; $I_C = -100\text{ }\mu\text{A}$	-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3\text{ V}$; $I_C = -10\text{ mA}$	-2.5	-1.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	
C_c	collector capacitance	$V_{CB} = -10\text{ V}$; $I_E = I_E = 0\text{ A}$; $f = 1\text{ MHz}$	-	-	3	pF
f_T	transition frequency	$V_{CE} = -5\text{ V}$; $I_C = -10\text{ mA}$; $f = 100\text{ MHz}$	[1] -	180	-	MHz

[1] Characteristics of built-in transistor.



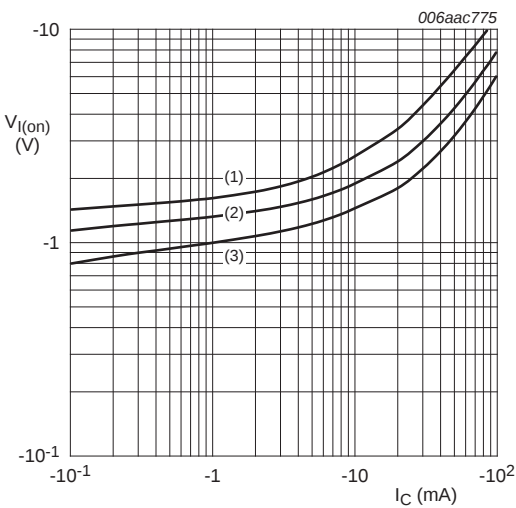
$V_{CE} = -5\text{ V}$
(1) $T_{amb} = 100^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -40^\circ\text{C}$

Fig 6. DC current gain as a function of collector current; typical values



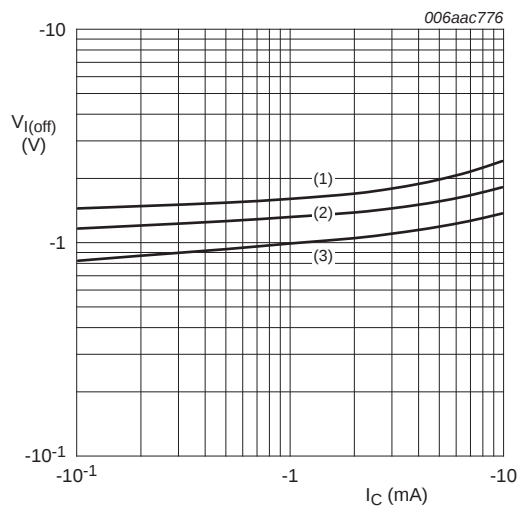
$I_C/I_B = 20$
(1) $T_{amb} = 100^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -40^\circ\text{C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



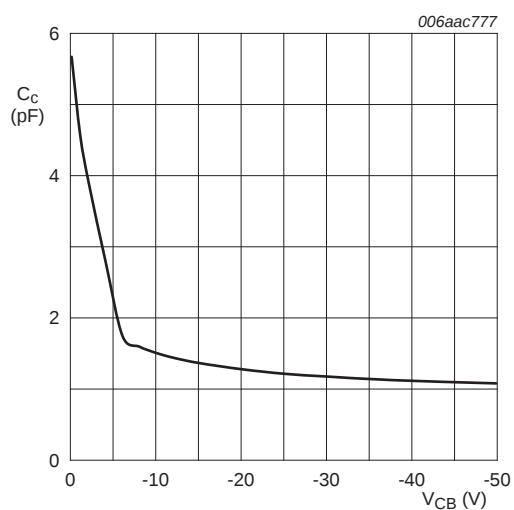
$V_{CE} = -0.3\text{ V}$
(1) $T_{amb} = -40^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 100^\circ\text{C}$

Fig 8. On-state input voltage as a function of collector current; typical values



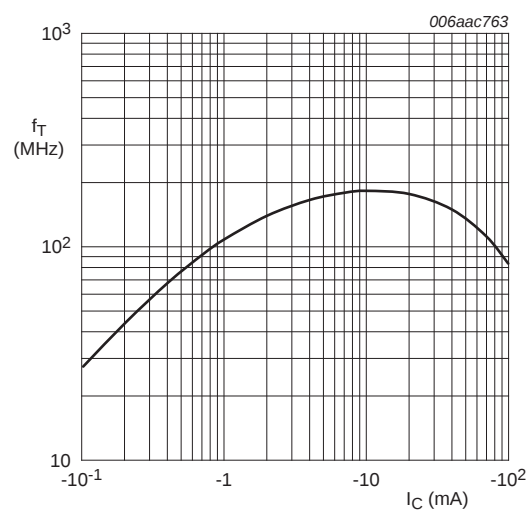
$V_{CE} = -5\text{ V}$
(1) $T_{amb} = -40^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 100^\circ\text{C}$

Fig 9. Off-state input voltage as a function of collector current; typical values



$f = 1 \text{ MHz}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 10. Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = -5 \text{ V}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

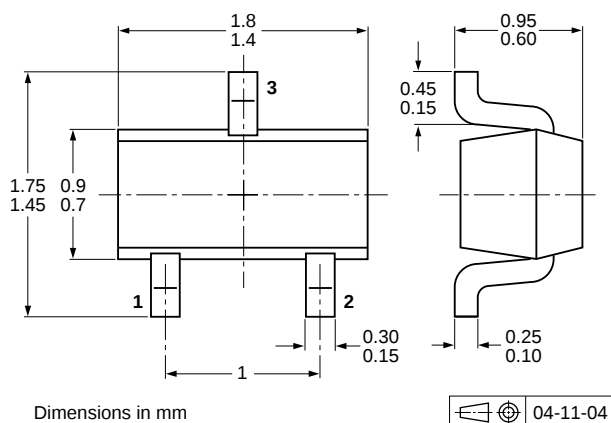


Fig 12. Package outline PDTA114EE (SOT416/SC-75)

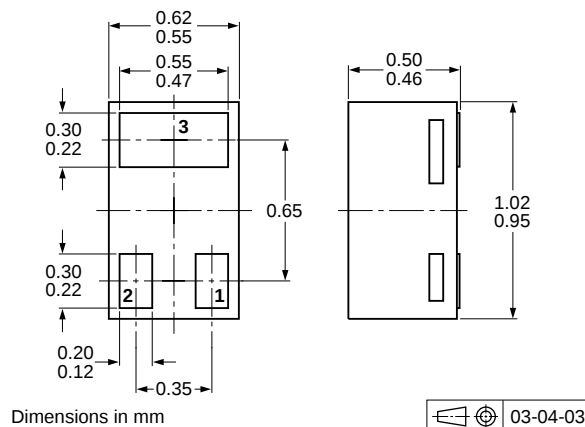


Fig 13. Package outline PDTA114EM (SOT883/SC-101)

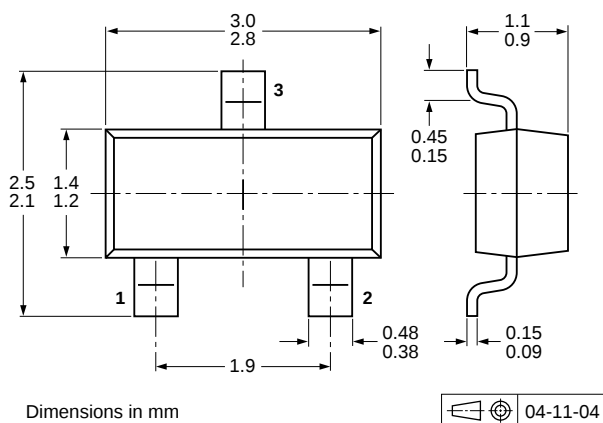


Fig 14. Package outline PDTA114ET (SOT23)

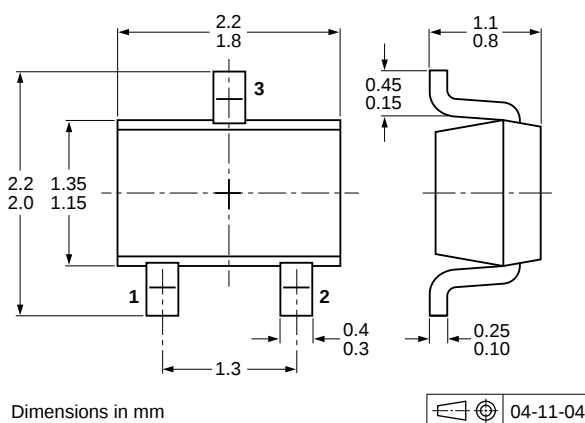


Fig 15. Package outline PDTA114EU (SOT323/SC-70)

10. Packing information

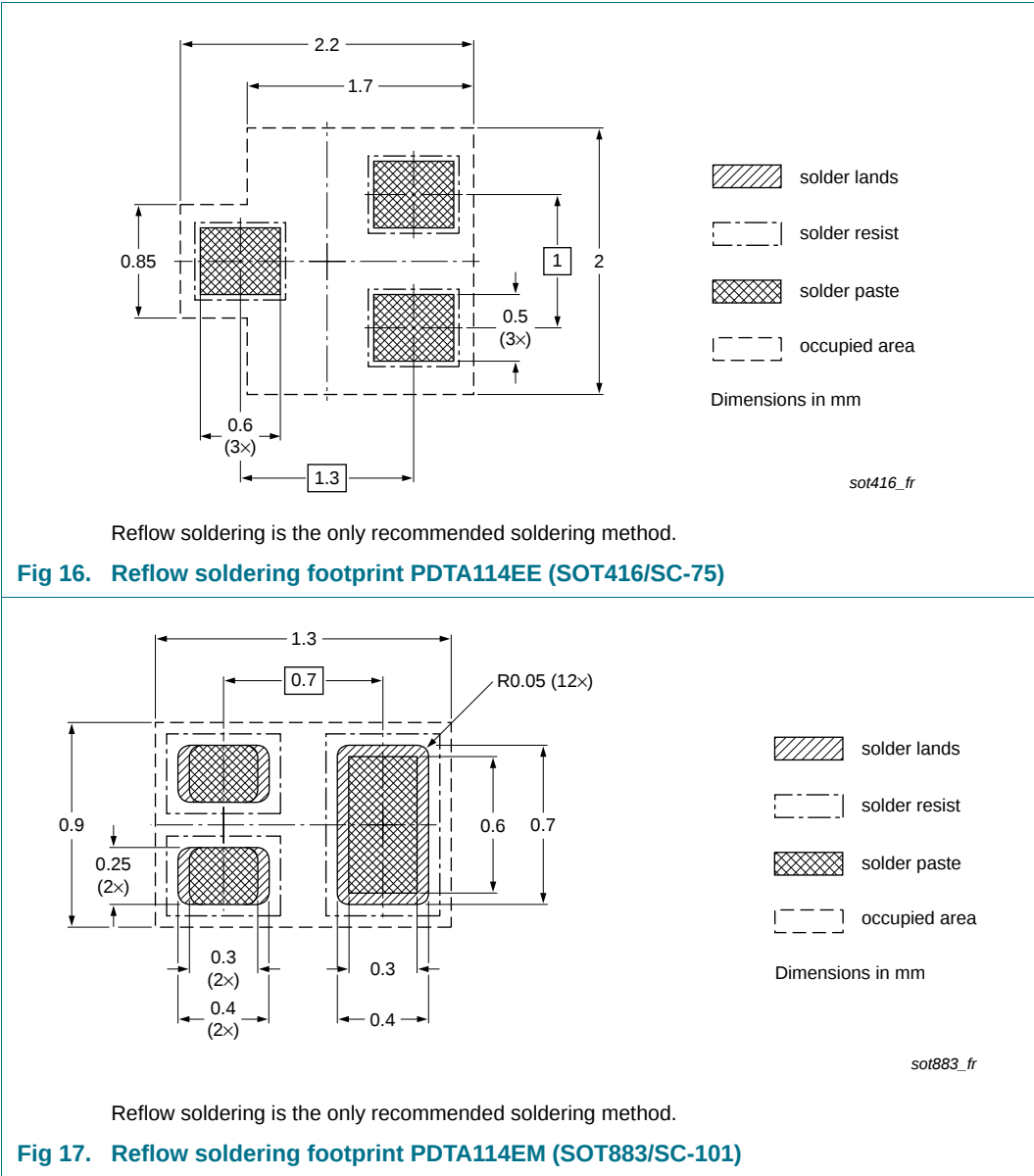
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PDTA114EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135
PDTA114EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315
PDTA114ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PDTA114EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering



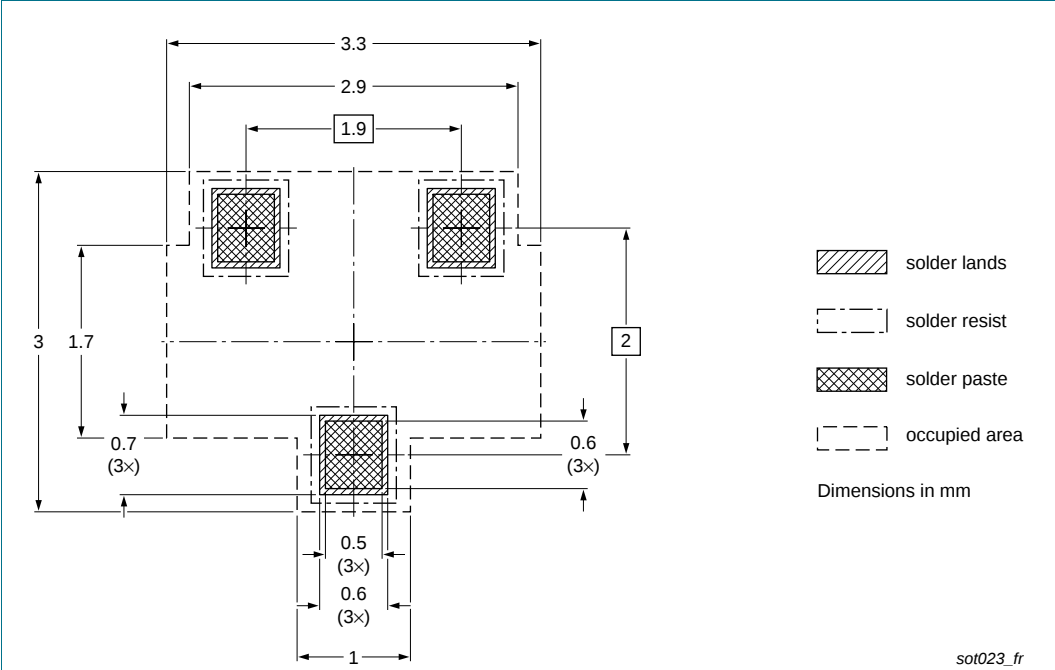


Fig 18. Reflow soldering footprint PDTA114ET (SOT23)

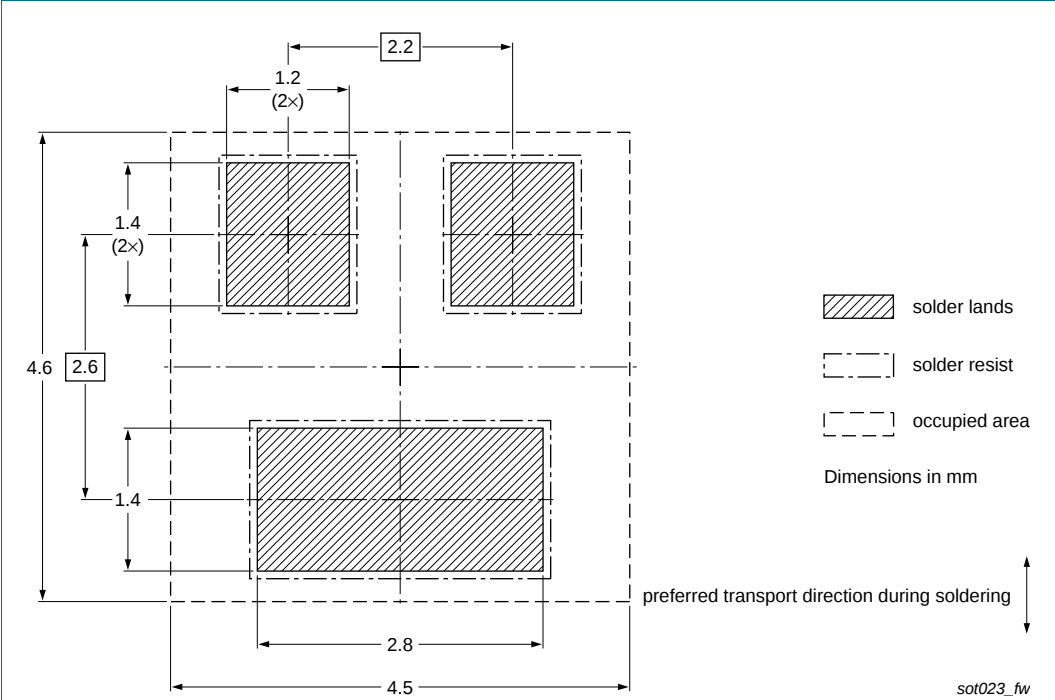
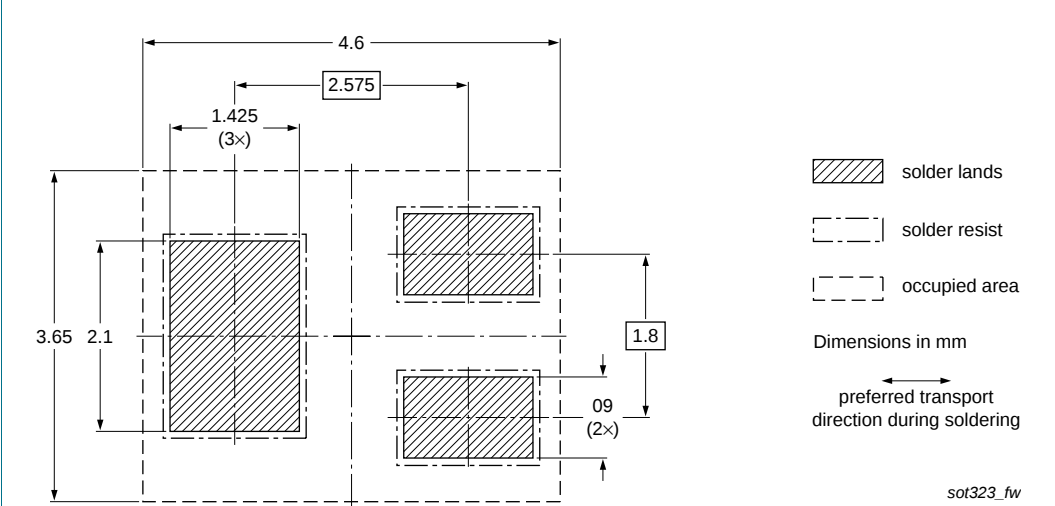
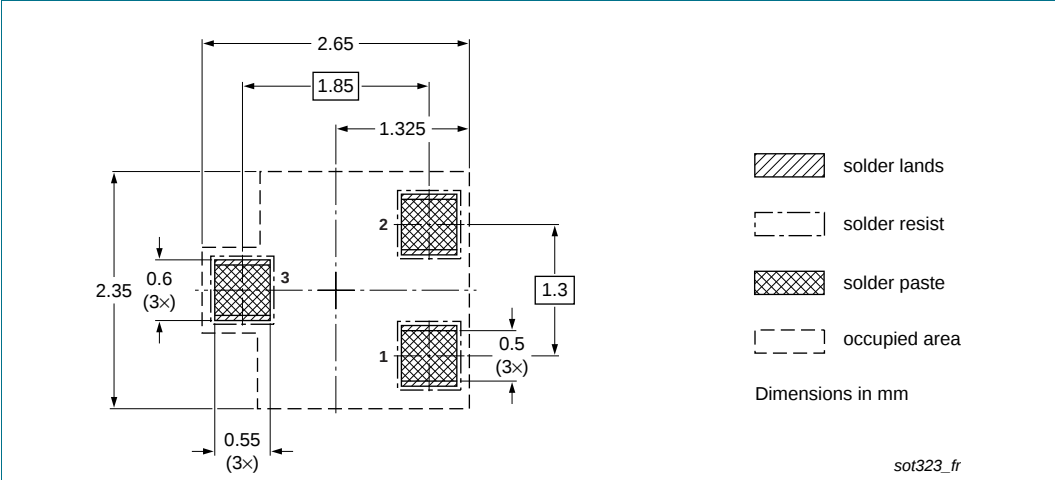


Fig 19. Wave soldering footprint PDTA114ET (SOT23)



12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA114E_SER v.10	20111221	Product data sheet	-	PDTA114E_SER v.9
Modifications:	• Figure 2 and 5 : corrected			
PDTA114E_SER v.9	20111122	Product data sheet	-	PDTA114E_SERIES v.8
PDTA114E_SERIES v.8	20040802	Product specification	-	PDTA114E_SERIES v.7
PDTA114E_SERIES v.7	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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15. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	7
8	Test information	9
8.1	Quality information	9
9	Package outline	10
10	Packing information	10
11	Soldering	11
12	Revision history	14
13	Legal information	15
13.1	Data sheet status	15
13.2	Definitions	15
13.3	Disclaimers	15
13.4	Trademarks	16
14	Contact information	16
15	Contents	17

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